## ESDE5V0U

Crownpo Technology



## DESCRIPTION

- The ESDE5VOU are designed by TVS device that is to protect sensitive electronics from damage or latch-up due to ESD.
- They are designed for use in applications where board space is at a premium.
- ESDE5VOU will protect single line, and may be used on line where the signal polarities swing above and below ground.
- ESDE5VOU offer desirable characteristics for board level protection including fast response time, low operating and clamping voltage, and no device degradation.
- ESDE5VOU may be used to meet the immunity requirements of IEC 61000-4-2, level 4.
- The small SOD-723 package makes them ideal for use in portable electronics such as cell phones, PDA's, notebook computers, and digital cameras.

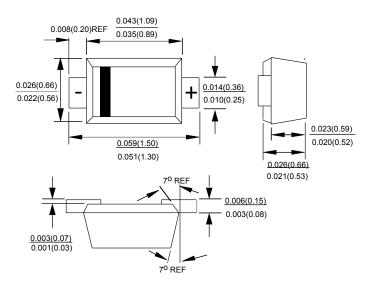
#### FEATURES

- Transient protection for data lines to IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact) IEC 61000-4-4 (EFT) 40A (5/50ns)
- Protects single I/O lines
- Working voltage: 5V
- Low leakage current
- Low operating and clamping voltages

#### APPLICATIONS

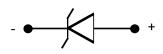
- Cellular Handsets and Accessories
- Cordless Phone
- PDA
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- MP3 Player

#### PACKAGE OUTLINE SOD-723

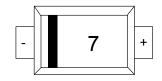


Unit : Inch (mm)

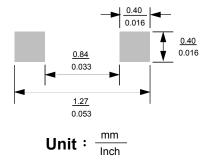
#### PINCONFIGURATION



#### **Part Marking**



# Suggested Pad Layout





## ABSOULTE MAXIMUM RATINGS

(TA= $25^{\circ}$ C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Peak Pulse Power ( $tp = 8/20 \ \mu s$ )	Ppk	135	W
Maximum Peak Pulse Current ( $tp = 8/20 \ \mu s$ )	Ipp	10	А
ESD per IEC 61000 – 4 – 2 (Air )	Vpp	±15	KV
ESD per IEC 61000 – 4 – 2 (Contact )	Vpp	$\pm 8$	KV
Operating Junction Temperature	Tı	-55 ~ 125	°C
Storage Temperature Range	Tstg	-55 ~ 150	°C
Lead Soldering Temperature	Tl	260 ( 10sec )	°C

# ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Тур	Max.	Unit
Reverse Stand – Off Voltage	Vrwm				5	V
Reverse Breakdown Voltage	VBR	It = 1mA	6		7.6	V
Reverse Leakage Current	Ir	$V_{RWM} = 5V$ , $T=25^{\circ}C$			1	μΑ
Clamping Voltage	Vc	Ipp =12A , tp = $8/20 \ \mu s$			13.5	V
Junction Capacitance	Cj	Between I/O Pin and GND $V_R = 0V$ , f = 1MHz			80	pF

## ORDERING INFORMATION

Part Number	Package	Part Marking	7" Reel Packing	
ESDE5VOU	SOD-723	7	8000 pcs	



## TYPICAL CHARACTERISTICS

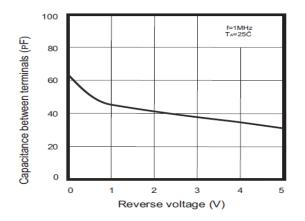
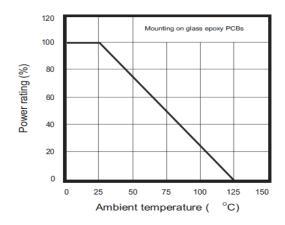


Fig 1 : Junction Capacitance V.S Reverse Voltage Applied





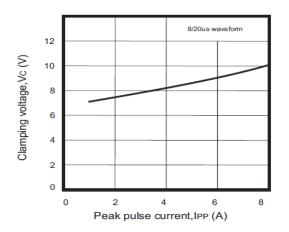


Fig 3 : Clamping Voltage VS Peak Pulse Current

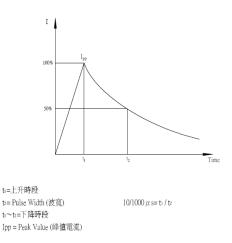


Fig 4 : Forward Voltage Drop V.S Peak Forward Current